

Apurba Chakraborty

List of Publications by Year in descending order

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26
papers

160
citations

1307366

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26
docs citations

26
times ranked

205
citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of temperature on radio frequency/linearity and harmonic distortion characteristics of Ge multi-channel fin shaped field-effect transistor. International Journal of RF and Microwave Computer-Aided Engineering, 2022, 32, e22987.	0.8	1
2	Effect of Positive/Negative Interface Trap Charges on the Performance of Multi Fin FinFET (M-FinFET). Silicon, 2022, 14, 8557-8566.	1.8	5
3	RF/Analog performance of GaAs Multi-Fin FinFET with stress effect. Microelectronics Journal, 2021, 117, 105267.	1.1	9
4	Temperature Dependent Linearity/Harmonic Analysis for FinFET and Gate All Around (GAA) Nanowire FET. , 2021, , .		0
5	Impact of stress effect on triple material gate step-FinFET with DC and AC analysis. Microsystem Technologies, 2020, 26, 1813-1821.	1.2	4
6	Effect of AlGa _N Barrier Thickness on Trapping Characteristics in AlGa _N /Ga _N Heterostructures. Springer Proceedings in Physics, 2019, , 183-186.	0.1	0
7	Elimination of V-shaped pits in InGa _N /Ga _N /Al _N /Ga _N heterostructure by metal modulation growth technique. Semiconductor Science and Technology, 2018, 33, 035009.	1.0	3
8	OFF-State Leakage and Current Collapse in AlGa _N /Ga _N HEMTs: A Virtual Gate Induced by Dislocations. IEEE Transactions on Electron Devices, 2018, 65, 1333-1339.	1.6	21
9	Effect of trapped charge in AlGa _N /Ga _N and AlGa _N /InGa _N /Ga _N heterostructure by temperature dependent threshold voltage analysis. Superlattices and Microstructures, 2018, 113, 147-152.	1.4	4
10	AlGa _N barrier thickness dependent surface and interface trapping characteristics of AlGa _N /Ga _N heterostructure. Chinese Journal of Physics, 2018, 56, 2365-2370.	2.0	0
11	Temperature-dependent short-channel parameters of FinFETs. Journal of Computational Electronics, 2018, 17, 1001-1012.	1.3	10
12	Reverse bias leakage current mechanism of AlGa _N /InGa _N /Ga _N heterostructure. Electronic Materials Letters, 2016, 12, 232-236.	1.0	8
13	Fowler-Nordheim Tunnelling Contribution in AlGa _N /Ga _N on Si (111) Schottky Current. IETE Technical Review (Institution of Electronics and Telecommunication Engineers, India), 2016, 33, 7-10.	2.1	1
14	Enhancement of two dimensional electron gas concentrations due to Si ₃ N ₄ passivation on Al _{0.3} Ga _{0.7} N/Ga _N heterostructure: strain and interface capacitance analysis. AIP Advances, 2015, 5, .	0.6	23
15	Simplified gas sensor model based on AlGa _N /Ga _N heterostructure Schottky diode. AIP Conference Proceedings, 2015, , .	0.3	4
16	Evolution and analysis of nitride surface and interfaces by statistical techniques: A correlation with RHEED through kinetic roughening. Electronic Materials Letters, 2015, 11, 707-716.	1.0	7
17	Temperature dependent etching of Gallium Nitride layers grown by PA-MBE. , 2015, , .		0
18	A novel growth strategy and characterization of fully relaxed un-tilted FCC GaAs on Si(100). Journal of Crystal Growth, 2015, 418, 138-144.	0.7	7

#	ARTICLE	IF	CITATIONS
19	Comparison of trap characteristics between AlGaIn/GaN and AlGaIn/InGaIn/GaN heterostructure by frequency dependent conductance measurement. Applied Physics Letters, 2015, 106, .	1.5	13
20	Quantitative investigation into the source of current slump in AlGaIn/GaN HEMT on both Si (111) and sapphire: Self-heating and trapping. AIP Conference Proceedings, 2015, , .	0.3	0
21	Comparison of different pathways in metamorphic graded buffers on GaAs substrate: Indium incorporation with surface roughness. Applied Surface Science, 2015, 324, 304-309.	3.1	12
22	Effects of threading dislocations on drain current dispersion and slow transients in unpassivated AlGaIn/GaN/Si heterostructure field-effect transistors. Applied Physics Letters, 2014, 105, .	1.5	11
23	Effect of longitudinal electric field and self heating of channel on linearity and gain of AlGaIn/GaN HEMT on Sapphire (0001). , 2014, , .		1
24	Growth and characterization of Al _{0.15} In _{0.15} Ga _{0.85} In _{0.05} As/GaAs pseudomorphic heterostructure by MBE. , 2014, , .		0
25	Comprehensive strain and band gap analysis of PA-MBE grown AlGaIn/GaN heterostructures on sapphire with ultra thin buffer. AIP Advances, 2014, 4, .	0.6	16
26	Investigation of Step Fin (SF), Step Drain (SD) and Step Source (SS) FinFETs with Trap Effect. IETE Journal of Research, 0, , 1-9.	1.8	0